

L Number	Hits	Search Text	DB	Time stamp
1	45797	((gallium near arsenide) GaAs) with (substrate wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 11:07
5	286	((indium near aluminum near arsenide) (indium near aluminum near gallium near arsenide) InAlAs InAlGaAs) with (barrier near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 11:14
6	896	((In."sub.y"G."sub1-y"As) (In."sub.x"G."sub1-x"As) InGaAs (indium near aluminum near arsenide)) with channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 11:14
7	150	(InAlAs (indium near aluminum near arsenide)) with schottky	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 11:15
8	12	((((gallium near arsenide) GaAs) with (substrate wafer)) and (((indium near aluminum near arsenide) (indium near aluminum near gallium near arsenide) InAlAs InAlGaAs) with (barrier near (layer film))) and (((In."sub.y"G."sub1-y"As) (In."sub.x"G."sub1-x"As) InGaAs (indium near aluminum near arsenide)) with channel) and ((InAlAs (indium near aluminum near arsenide)) with schottky)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/02 11:15